

MegaMOS™ FET

IXTH 30N50

N-Channel Enhancement Mode

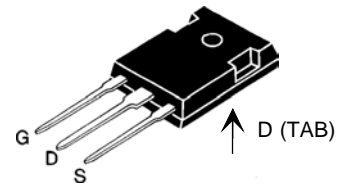
$$V_{DSS} = 500 \text{ V}$$

$$I_{D(\text{cont})} = 30 \text{ A}$$

$$R_{DS(\text{on})} = 0.17 \text{ } \Omega$$



Symbol	Test Conditions	Maximum Ratings	TO-247 AD
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	500 V	
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	500 V	
V_{GS}	Continuous	± 20 V	
V_{GSM}	Transient	± 30 V	
I_{D25}	$T_C = 25^\circ\text{C}$	30 A	
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	120 A	
P_D	$T_C = 25^\circ\text{C}$	360 W	
T_J		-55 ... +150 $^\circ\text{C}$	
T_{JM}		150 $^\circ\text{C}$	
T_{stg}		-55 ... +150 $^\circ\text{C}$	
T_L	1.6 mm (0.063 in) from case for 10 s	300 $^\circ\text{C}$	
M_d	Mounting torque	1.13/10 Nm/lb.in.	
Weight		6 g	



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard package JEDEC TO-247 AD
- Low $R_{DS(\text{on})}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Fast switching times

Applications

- Switch-mode and resonant-mode power supplies
- Motor controls
- Uninterruptible Power Supplies (UPS)
- DC choppers

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

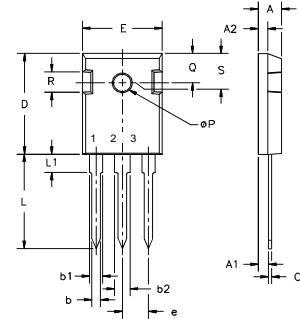
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 5 \text{ mA}$ BV_{DSS} temperature coefficient	500	.087	V %/k
$V_{GS(\text{th})}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ } \mu\text{A}$ $V_{GS(\text{th})}$ temperature coefficient	2	-0.25	V %/k
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			200 μA 3 mA
$R_{DS(\text{on})}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ 30N50 Pulse test, $t \leq 300 \text{ } \mu\text{s}$, duty cycle $d \leq 2 \%$			0.17 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	18	28	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		5680	pF
C_{oss}			635	pF
C_{rss}			240	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 1\ \Omega$, (External)		35	ns
t_r			42	ns
$t_{d(off)}$			110	ns
t_f			26	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		227	nC
Q_{gs}			29	nC
Q_{gd}			110	nC
R_{thJC}			0.35	K/W
R_{thCK}		0.15		K/W

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			30 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			120 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		850	ns

TO-247 AD Outline



Terminals: 1 - Gate 2 - Drain
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC